

# GSMDS2305

## 20V P-Channel MOSFETs

### Product Description

These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency fast switching applications.

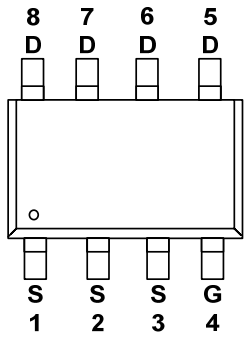
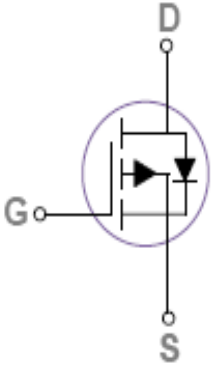
### Features

- -20V, -11A,  $R_{DS(ON)}=16m\Omega@V_{GS}=-4.5V$
- Improved dv/dt capability
- Fast switching
- Suit for -1.8V Gate Drive Applications
- Green Device Available
- SOP-8 package design

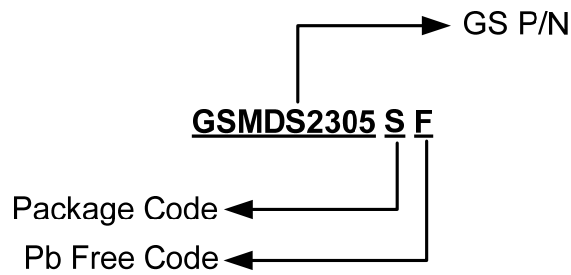
### Applications

- Notebook
- Load Switch
- Networking

### Packages & Pin Assignments

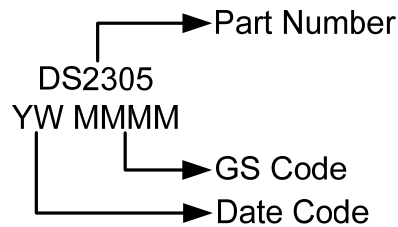
GSMDS2305SF (SOP-8)			
			
			
Pin	Description	Pin	Description
1	Source	5	Drain
2	Source	6	Drain
3	Source	7	Drain
4	Gate	8	Drain

## Ordering Information



Part Number	Package	Quantity Reel
GSMD S2305 SF	SOP-8	4000 PCS

## Marking Information



## Absolute Maximum Ratings

$T_A=25^{\circ}\text{C}$  Unless otherwise noted

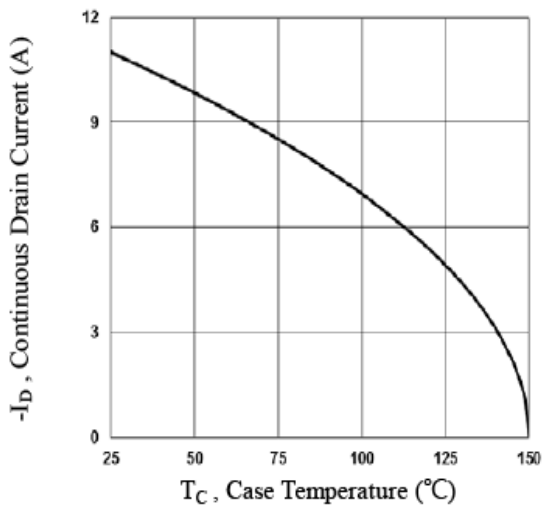
Symbol	Parameter	Typical	Unit
$V_{DS}$	Drain-Source Voltage	-20	V
$V_{GS}$	Gate-Source Voltage	$\pm 10$	V
$I_D$	Continuous Drain Current	$T_A=25^{\circ}\text{C}$	-11
		$T_A=100^{\circ}\text{C}$	-7
$I_{DM}$	Pulsed Drain Current	-44	A
$P_D$	Power Dissipation ( $T_A=25^{\circ}\text{C}$ )	2.5	W
	Power Dissipation (Derate above $25^{\circ}\text{C}$ )	0.02	W/ $^{\circ}\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to +150	$^{\circ}\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to +150	$^{\circ}\text{C}$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	50	$^{\circ}\text{C}/\text{W}$

## Electrical Characteristics

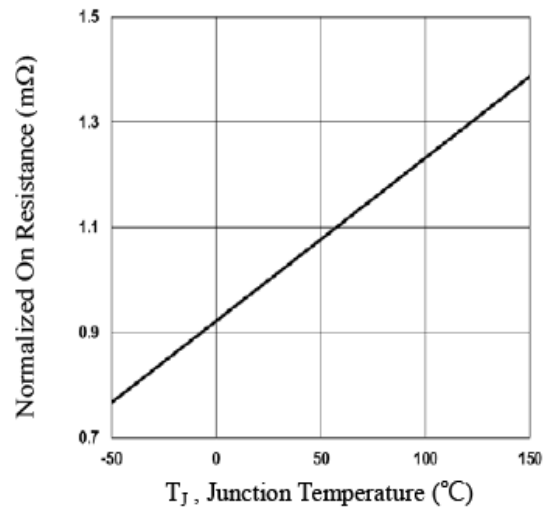
T<sub>A</sub>=25°C Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-20			V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA		-0.01		V/°C
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.3	-0.6	-1.0	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient			3		mV/°C
I <sub>GSS</sub>	Gate Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±10V			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V			-1	μA
		V <sub>DS</sub> =-16V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C			-10	
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current			-11	A
I <sub>SM</sub>	Pulsed Source Current				-44	
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-6A		12	16	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-4A		16	22	
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-3A		21	28	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-10V, I <sub>D</sub> =-6A		20		S
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A			-1	V
<b>Dynamic</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-6A		27	40	nC
Q <sub>gs</sub>	Gate-Source Charge			2.4	4.8	
Q <sub>gd</sub>	Gate-Drain Charge			5.3	8	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHz		2320	3370	pF
C <sub>oss</sub>	Output Capacitance			280	410	
C <sub>rss</sub>	Reverse Transfer Capacitance			175	260	
t <sub>d(on)</sub>	Turn-On Time	V <sub>DD</sub> =-10V, I <sub>D</sub> =-1A, V <sub>GS</sub> =-4.5V, R <sub>G</sub> =25Ω		16.2	31	ns
t <sub>r</sub>				43.5	83	
t <sub>d(off)</sub>	Turn-Off Time			114	217	
t <sub>f</sub>				28.8	55	

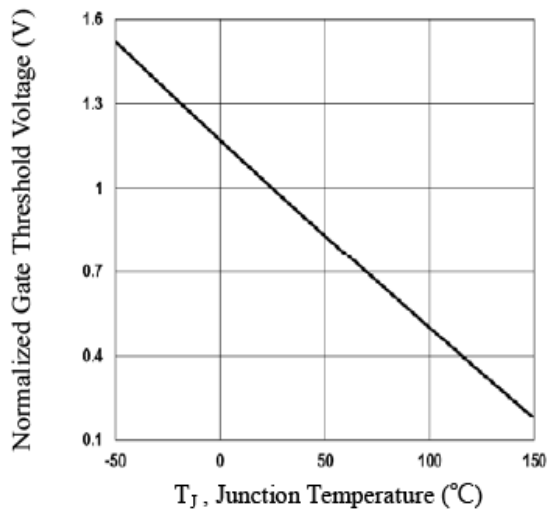
## Typical Performance Characteristics



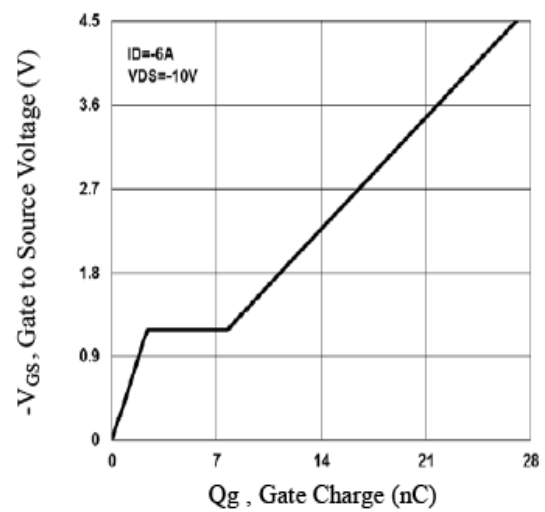
**Fig.1 Continuous Drain Current vs.  $T_c$**



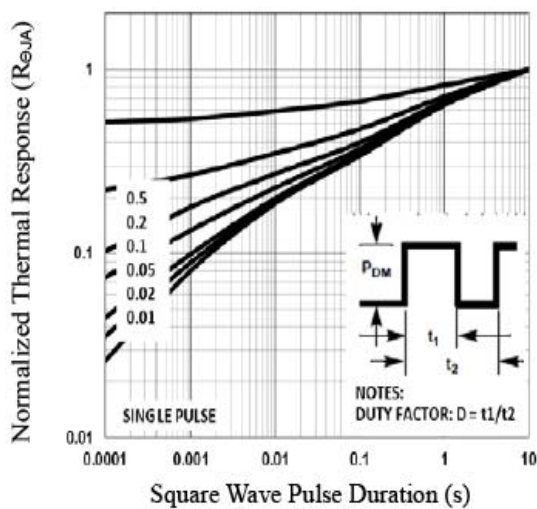
**Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_j$**



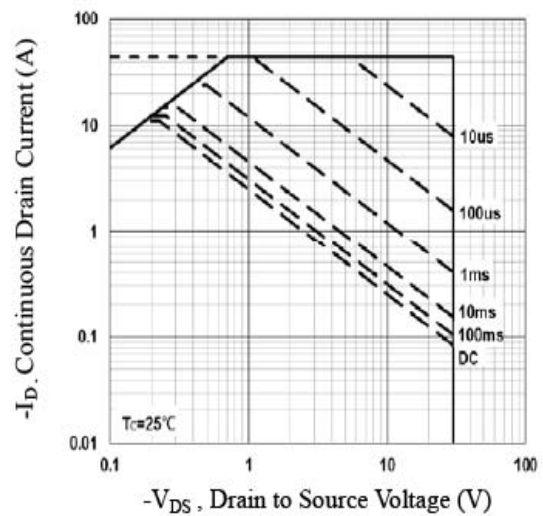
**Fig.3 Normalized  $V_{th}$  vs.  $T_j$**



**Fig.4 Gate Charge Waveform**



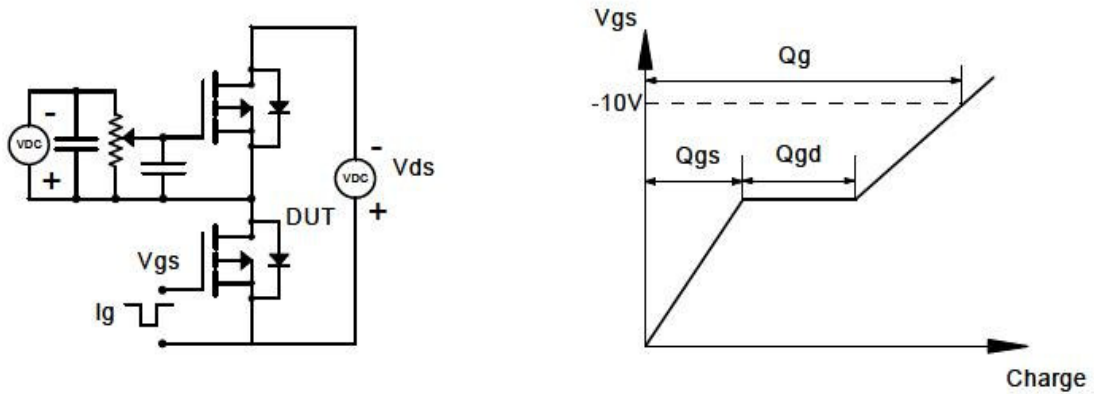
**Fig.5 Normalized Transient Response**



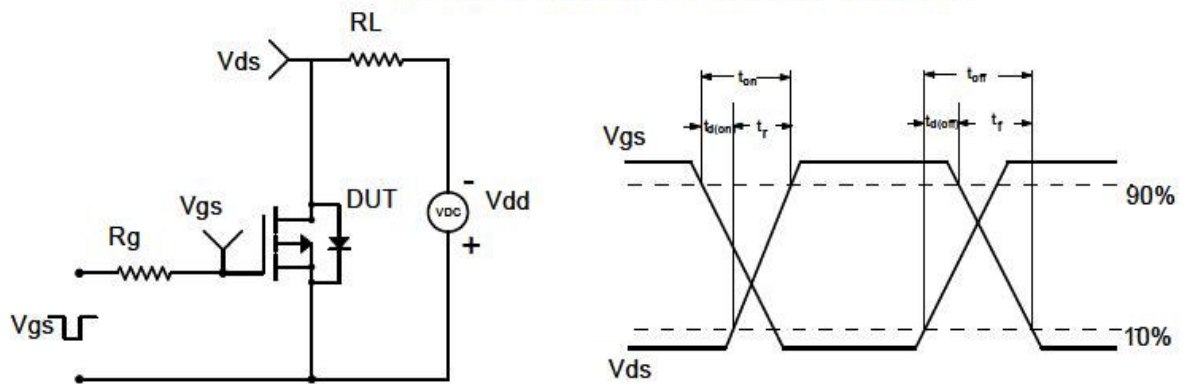
**Fig.6 Maximum Safe Operation Area**

## Typical Performance Characteristics (Continue)

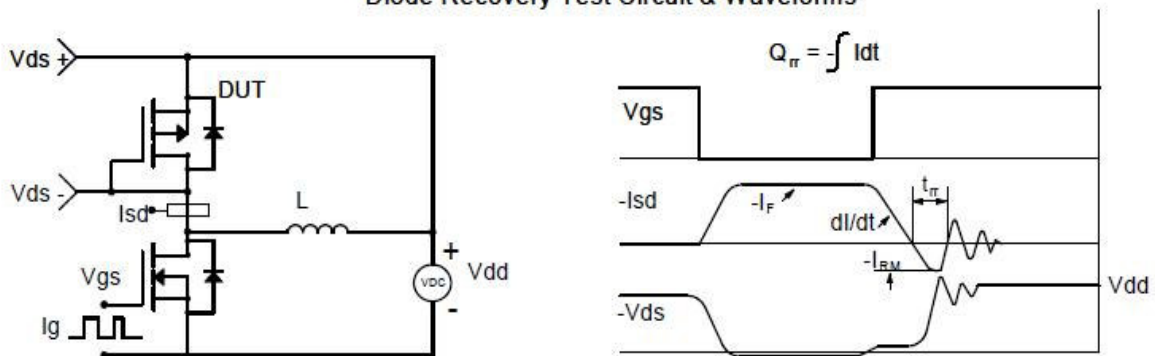
### Gate Charge Test Circuit & Waveform



### Resistive Switching Test Circuit & Waveforms

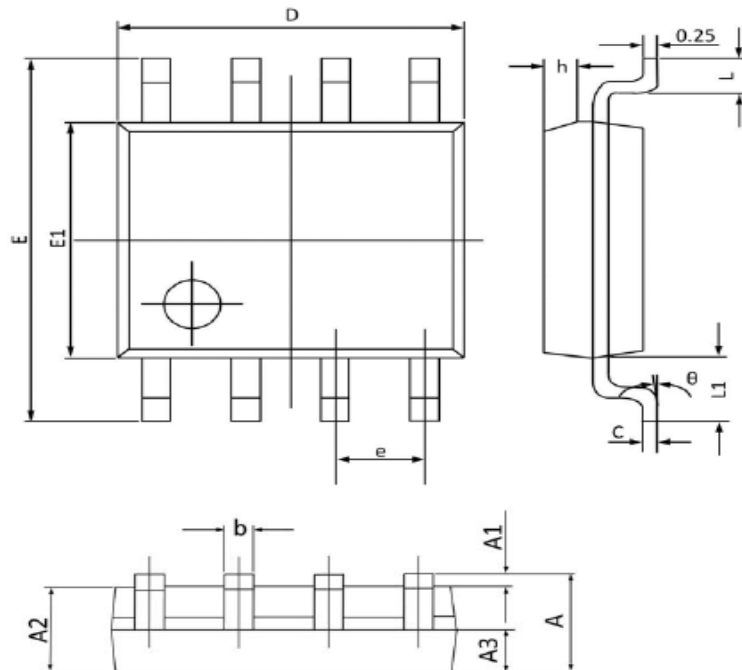


### Diode Recovery Test Circuit & Waveforms



## Package Dimension

### SOP-8










Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.068
A1	0.100	0.250	0.004	0.009
A2	1.300	1.500	0.052	0.059
A3	0.600	0.700	0.024	0.027
b	0.390	0.480	0.016	0.018
c	0.210	0.260	0.009	0.010
D	4.700	5.100	0.186	0.200
E	5.800	6.200	0.229	0.244
E1	3.700	4.100	0.146	0.161
e	1.270 (BSC)		0.050 (BSC)	
h	0.250	0.500	0.010	0.019
L	0.500	0.800	0.019	0.031
L1	1.050 (BSC)		0.041 (BSC)	
θ	0°	8°	0°	8°



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